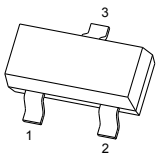
JSMICRO
SEMICONDUCTOR

JSM3420S

N-Channel 20-V(D-S) MOSFET

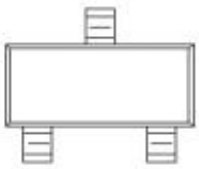
$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
20V	0.024Ω@10V	6.0A
	0.027Ω@4.5V	
	0.035Ω@2.5V	

SOT-23

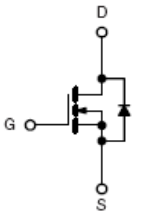


1.GATE
2.SOURCE
3.DRAIN

MARKING



Equivalent Circuit



General FEATURE

- TrenchFET Power MOSFET
- Lead free product is acquired
- Surface mount package

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	
Continuous Drain Current	I_D	6.0	A
Pulsed Drain Current*1	I_{DM}	20	
Continuous Source-Drain Diode Current	I_S	1.25	
Maximum Power Dissipation	P_D	1.25	W
Thermal Resistance from Junction to Ambient(t ≤10s)	$R_{\theta JA}$	100	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~+150	

Note :

*1. Pulse Width ≤ 300μs, Duty cycle ≤2%

MOSFET ELECTRICAL CHARACTERISTICS

T_a =25℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	20			V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D = 250μA	0.5	0.8	1.0	V
Gate-source leakage	I_{GSS}	V_{DS} =0V, V_{GS} =±12V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} =16V, V_{GS} =0V			100	nA
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} =10V, I_D =6A		0.016	0.024	Ω
		V_{GS} =4.5V, I_D =5A		0.019	0.027	
		V_{GS} =2.5V, I_D =4A		0.023	0.035	
Forward transconductance [a]	g_{fs}	V_{DS} =5V, I_D =6A		25	-	S
Dynamic[b]						
Input capacitance	C_{iss}	V_{DS} =15V,V_{GS} =0V,f =1MHz		742		pF
Output capacitance	C_{oss}			66		
Reverse transfer capacitance	C_{rss}			78		
Total gate charge	Q_g	V_{DS} =10V,V_{GS} =4.5V,I_D =6A		9.0		nC
Gate-source charge	Q_{gs}			1.5		
Gate-drain charge	Q_{gd}			2.6		
Turn-on delay time	$t_{d(on)}$	V_{DD}=10V,I_D =1A V_{GEN}=4.5V,Rg=6Ω		12.0		ns
Rise time	t_r			23.0		
Turn-off delay time	$t_{d(off)}$			14.0		
Fall time	t_f			9.0		
Drain-source body diode characteristics						
Continuous source-drain diode current	I_S	T_C=25℃			1.25	A
Body diode voltage	V_{SD}	I_S=1.0A		0.7	1.0	V

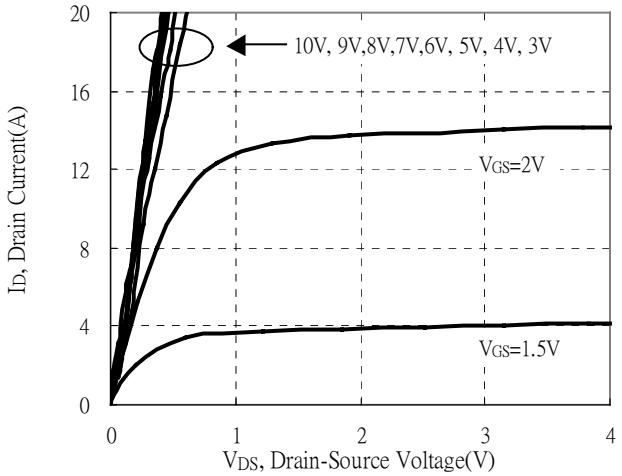
Notes :

a.Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

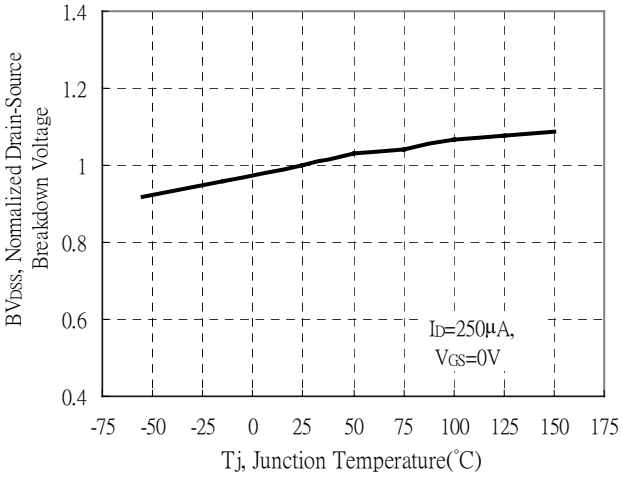
b.Guaranteed by design, not subject to production testing.

Typical Characteristics

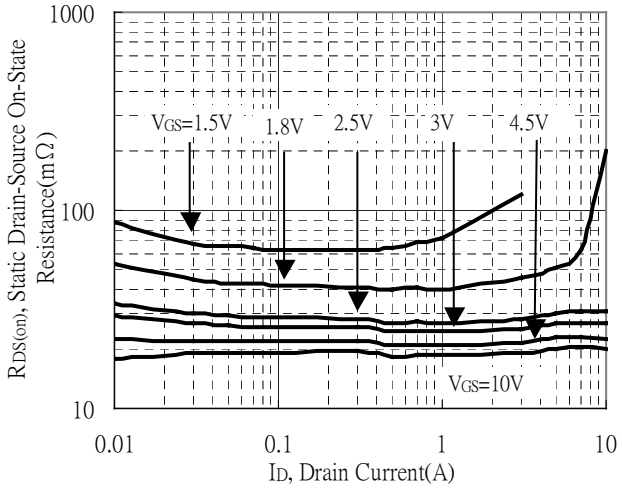
Typical Output Characteristics



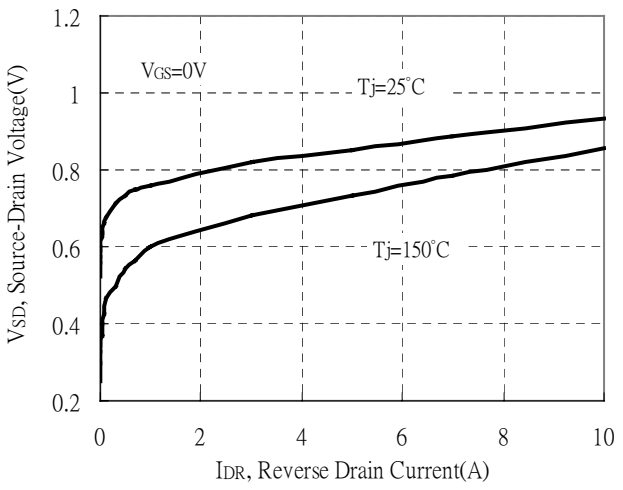
Brekdown Voltage vs Ambient Temperature



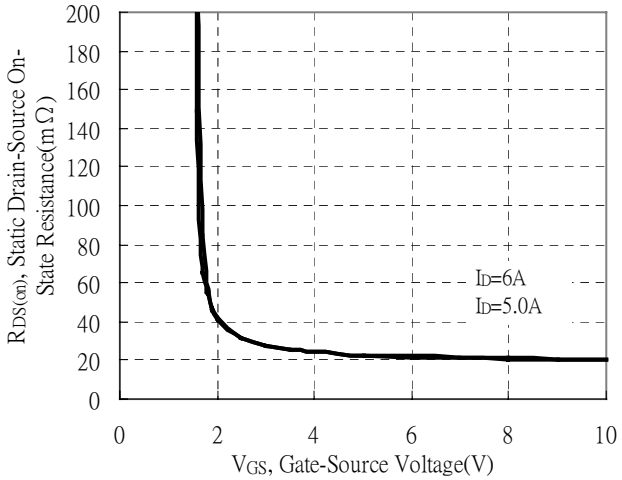
Static Drain-Source On-State resistance vs Drain Current



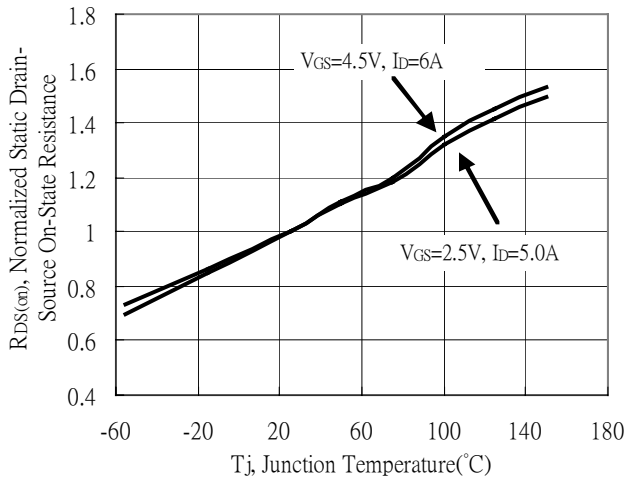
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

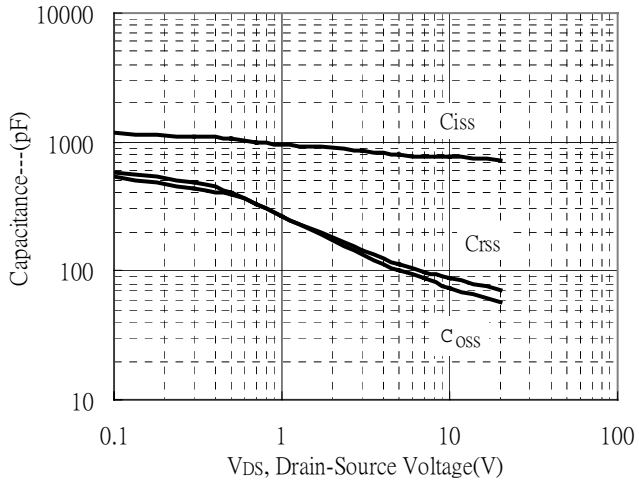


Drain-Source On-State Resistance vs Junction Tempearture

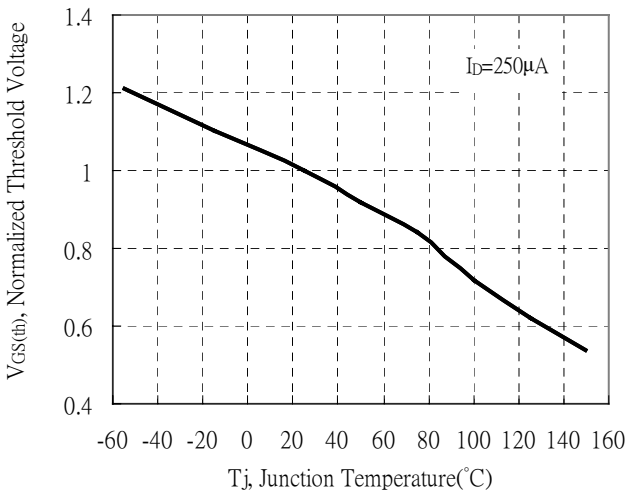


Typical Characteristics(Cont.)

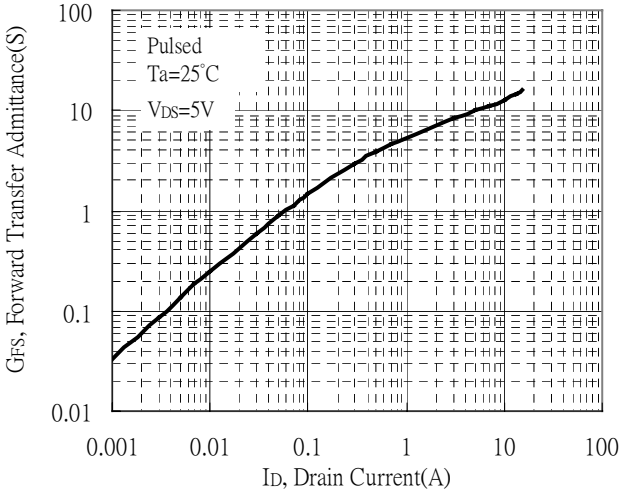
Capacitance vs Drain-to-Source Voltage



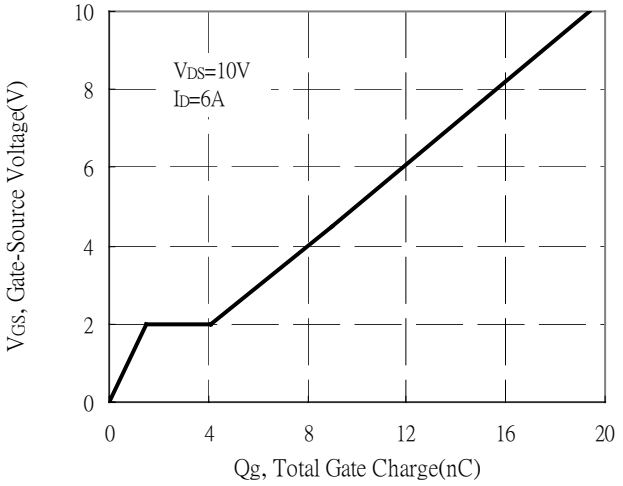
Threshold Voltage vs Junction Tempearture



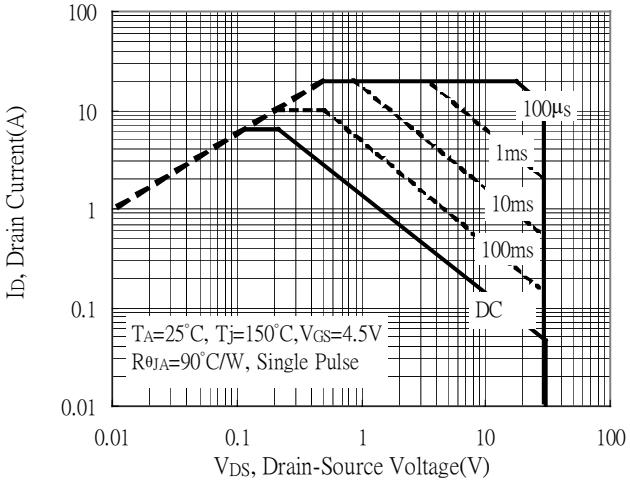
Forward Transfer Admittance vs Drain Current



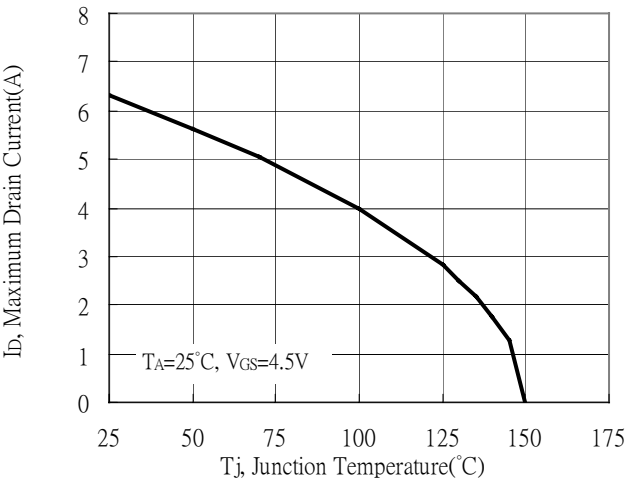
Gate Charge Characteristics



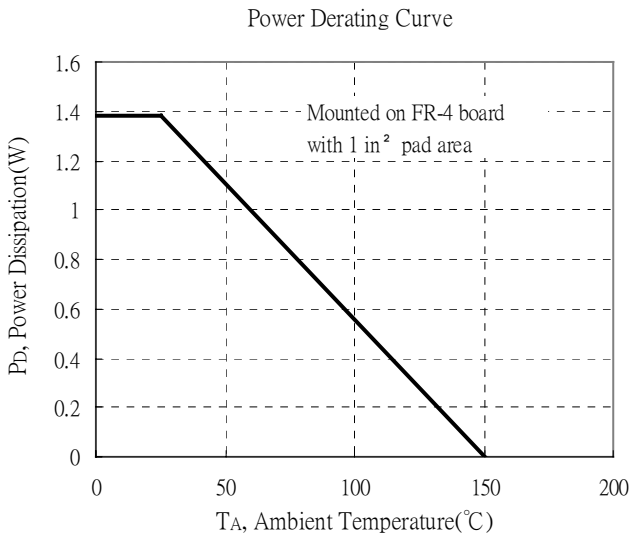
Maximum Safe Operating Area

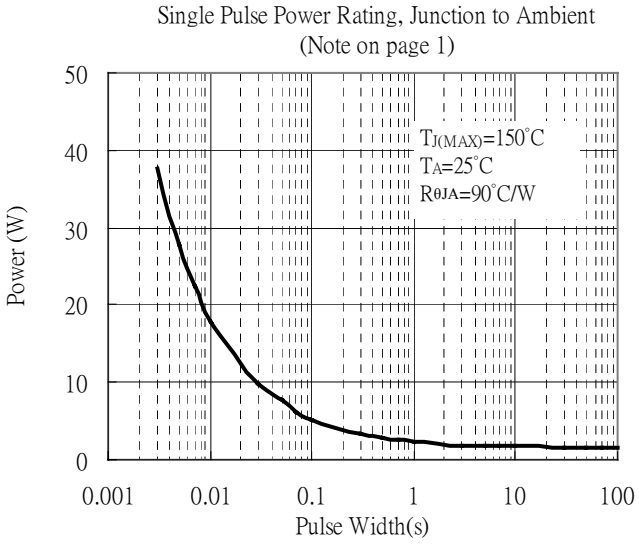


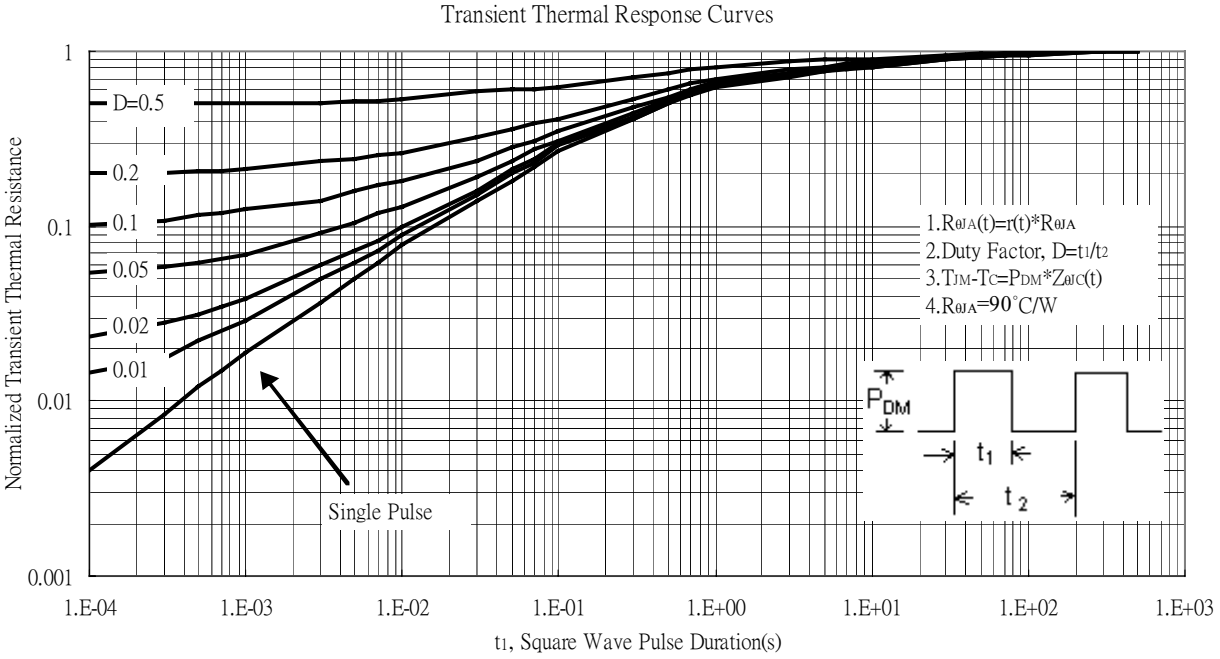
Maximum Drain Current vs JunctionTemperature



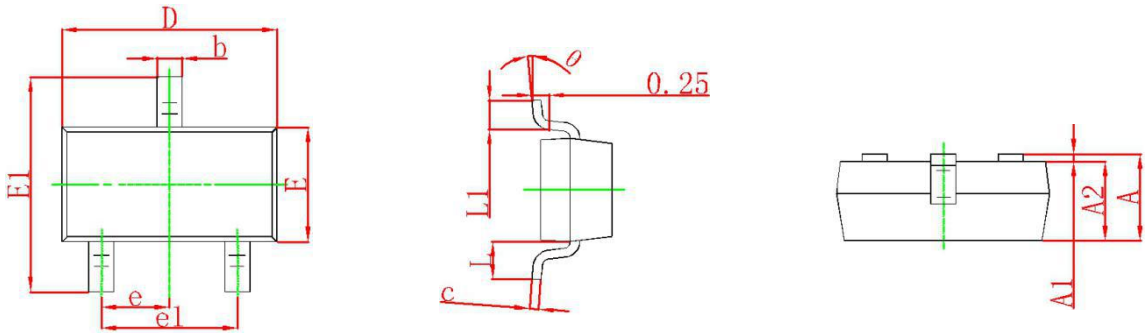
Typical Characteristics(Cont.)





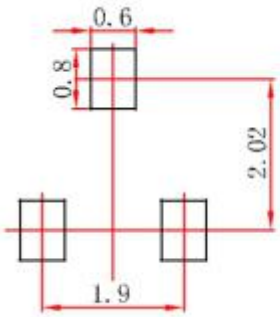


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.